Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claims 1-5 (Canceled)

Claim 6 (Currently Amended): A semiconductor device comprising:

first and second gates formed on active regions of a substrate, said first and second gates each consisting of a refractory metal layer on a polysilicon layer and each having side surfaces;

a field oxide formed on the substrate between said first and second gates;

a protective layer formed directly on said field oxide to prevent overetching of said field oxide, said protective layer being a conductive layer, having side surfaces thereof over said field oxide, and having substantially uniform ~~thickeness~~ thickness;

sidewall spacers of silicon oxide film formed on the side surfaces of said first and second gates; and

an insulating layer, a contact hole, and a connecting wire formed above a surface of the substrate.

Claim 7 (Previously Presented): The semiconductor device of claim 6, wherein said protective layer is a polysilicon layer.

Claim 8 (Canceled)

Claim 9 (Previously Presented): The semiconductor device of claim 6, wherein said first and second gates are MOSFET gates.

Claim 10 (Canceled)

Claim 11 (Previously Presented): A semiconductor device comprising:

a gate formed on an active region of a substrate, said gate having side surfaces;

a field oxide formed on the substrate adjacent the active region;

a protective layer formed directly on said field oxide to prevent overetching of said field oxide, said protective layer being a conductive layer, having side surfaces thereof over said field oxide, and having substantially uniform thickness;

sidewall spacers formed on the side surfaces of said gate; and

an insulating layer, a contact hole, and a connecting wire formed above a surface of the substrate,

said protective layer being formed on said field oxide only.

Claim 12 (Previously Presented): The semiconductor device of claim 11, wherein said protective layer is a polysilicon layer.

Claim 13 (Previously Presented): The semiconductor device of claim 11, wherein said gate is a MOSFET gate.

Claim 14 (Canceled)

Claim 15 (Previously Presented): The semiconductor device of claim 11, further comprising an additional gate formed on the substrate, said field oxide being formed on the substrate between said gate and said additional gate.

Claim 16 (Previously Presented): A semiconductor device comprising:

a gate formed on an active region of a substrate, said gate consisting of a refractory metal layer on a polysilicon layer and having side surfaces;

a field oxide formed on the substrate adjacent the active region;

a protective layer formed directly on said field oxide to prevent overetching of said field oxide, said protective layer being a conductive layer, having side surfaces thereof over said field oxide, and having substantially uniform thickness;

sidewall spacers of silicon oxide film formed on the side surfaces of said gate; and

an insulating layer, a contact hole, and a connecting wire formed above a surface of the substrate,

said protective layer being formed on said field oxide only.

Claim 17 (Previously Presented): The semiconductor device of claim 16, wherein said protective layer is a polysilicon layer.

Claim 18 (Previously Presented): The semiconductor device of claim 16, wherein said gate is a MOSFET gate.

Claim 19 (Previously Presented): The semiconductor device of claim 16, further comprising an additional gate formed on the substrate, said field oxide being formed on the substrate between said gate and said additional gate.